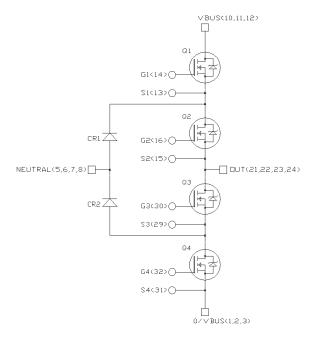
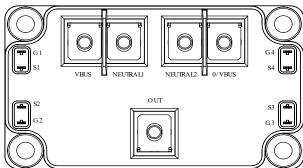
MSCSM170TLM15CAG

Three Level Inverter SiC MOSFET Power Module

Product Overview

The MSCSM170TLM15CAG device is a three level inverter 1700V/179A silicon carbide (SiC) MOSFET power module.





Note: All ratings at $T_J = 25$ °C, unless otherwise specified.

⚠ CAUTION

These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM170TLM15CAG device:

- · SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- · SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- · Low stray inductance
- · Kelvin source for easy drive
- · High level of integration
- · Aluminum nitride (AIN) substrate for improved thermal performance
- · M5 power connectors

Benefits

The following are the benefits of MSCSM170TLM15CAG device:

- · Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- · Low profile
- RoHS Compliant

Application

The MSCSM170TLM15CAG device is designed for the following applications:

- · Uninterruptible power supplies
- Solar converter

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM170TLM15CAG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM170TLM15CAG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V _{DSS}	Drain-Source voltage		1700	V
I _D			179	Α
			142	
I _{DM}	Pulsed drain current		360	
V _{GS}	Gate-Source voltage		-10/23	V
R _{DS(on)}	Drain-Source ON resistance		15	mΩ
P _D	Power dissipation	T _C = 25 °C	843	W

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM170TLM15CAG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0V; V _{DS} = 1700V		_	30	300	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20V	T _J = 25 °C	_	11.7	15	mΩ
	resistance I _D = 90A	T _J = 175 °C	_	20.8	_		
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}; I_D = 7.5 \text{ mA}$		1.8	3.2	_	V
I _{GSS}	Gate–Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$		_	_	300	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM170TLM15CAG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance	V _{GS} = 0V		_	9900	_	pF
C _{oss}	Output capacitance	V _{DS} = 1000V		_	450	_	
C _{rss}	Reverse transfer capacitance	f = 1 MHz		_	30	_	
Q_g	Total gate charge	V _{GS} = -5V/20V		_	534	_	nC
Q _{gs}	Gate-source charge	V _{Bus} = 850V		_	147	_	
Q _{gd}	Gate-drain charge	I _D = 90A		_	81	_	
T _{d(on)}	Turn-on delay time	V _{GS} = -5V/20V	T _J = 150 °C	_	75	_	ns
T _r	Rise time	V _{Bus} = 900V		_	75	_	
T _{d(off)}	Turn-off delay time	I _D = 150A		_	153	_	
T _f	Fall time	$R_{G(on)} = 9.4\Omega$ $R_{G(off)} = 5.4\Omega$			56	_	
Eon	Turn-on energy	V _{GS} = -5V/20V	T _J = 150 °C	_	6.7	_	mJ
E _{off}	Turn-off energy	$V_{Bus} = 900V$ $I_{D} = 150A$ $R_{G(on)} = 9.4\Omega$ $R_{G(off)} = 5.4\Omega$	T _J = 150 °C	_	3.6	_	
R _{Gint}	Internal gate resistance			_	1.95	_	Ω
R _{thJC}	Junction-to-case therm	nal resistance		_	_	0.178	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM170TLM15CAG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{SD}	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 90A$	_	3.7	_	V
		$V_{GS} = -5V; I_{SD} = 90A$	_	3.9	_	
t _{rr}	Reverse recovery time	$I_{SD} = 90A; V_{GS} = -5V$	_	27	_	ns
Q _{rr}	Reverse recovery charge	$V_R = 900V$; $di_F/dt = 3000 A/\mu s$	_	1950	_	nC
Irr	Reverse recovery current		_	138	_	Α

1.2 CR1 and CR2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the CR1 and CR2 SiC diode ratings and characteristics per SiC diode of MSCSM170TLM15CAG device.

Table 1-5. SiC Schottky Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min.	Тур.	Max.	Unit
V _{RRM}	Peak repetitive reverse volt	age		_	_	1700	V
I _{RRM}	Reverse leakage current V _R = 1700V	T _J = 25 °C	_	30	600	μA	
			T _J = 175 °C	_	450	_	
I _F	DC forward current	_	T _C = 125 °C	_	90	_	Α
V _F	Diode forward voltage I _F = 90A	I _F = 90A	T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C	_	2.3	_	
Q _C	Total capacitive charge	V _R = 900V		_	690	_	nC
С	Total capacitance	$f = 1 \text{ MHz}, V_R = 600V$ $f = 1 \text{ MHz}, V_R = 900V$		_	501	_	pF
				_	414	_	
R _{thJC}	Junction-to-case thermal re	sistance		_	_	0.197	°C/W

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM170TLM15CAG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristics			Min.	Max.	Unit
V _{ISOL}	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			4000	_	V
T _J	Operating junction temperature range			-40	175	°C
T _{JOP}	Recommended junction temperature un	Recommended junction temperature under switching conditions			T _{Jmax} -25	
T _{STG}	Storage temperature range			-40	125	
T _C	Operating case temperature			-40	125	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight			_	300	g

1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM170TLM15CAG device.

Figure 1-1. Maximum Thermal Impedance

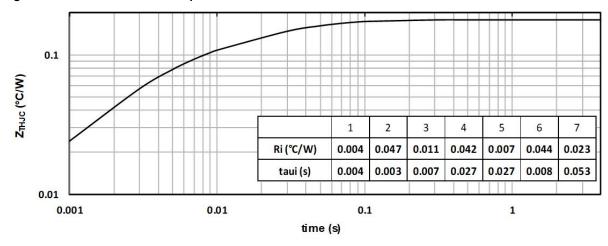


Figure 1-2. Output Characteristics, $T_J = 25$ °C

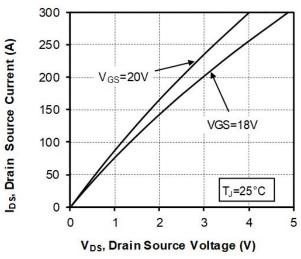


Figure 1-3. Output Characteristics, T_J = 175 °C

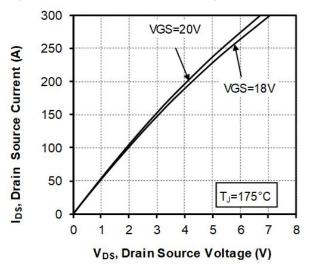


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

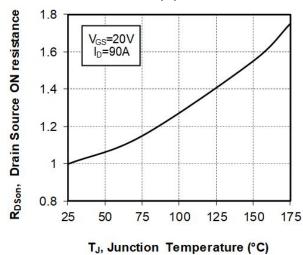


Figure 1-5. Transfer Characteristics

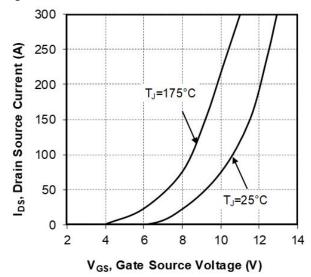


Figure 1-6. Switching Energy vs. Rg

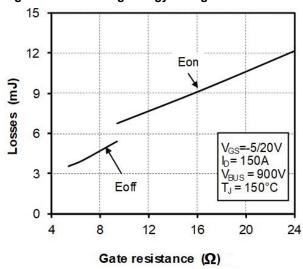


Figure 1-7. Switching Energy vs. Current

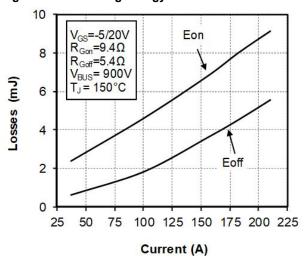


Figure 1-8. Capacitance vs. Drain Source Voltage

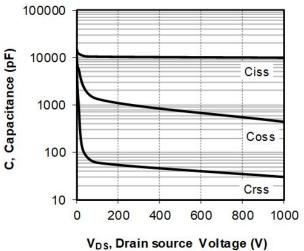


Figure 1-9. Gate Charge vs. Gate Source Voltage

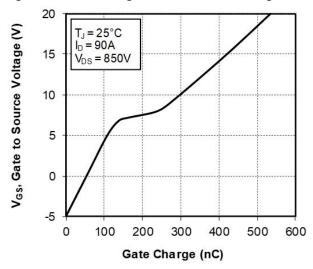


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

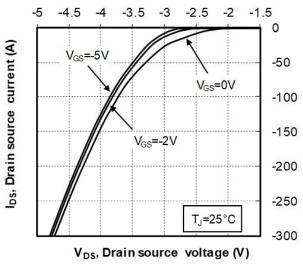


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

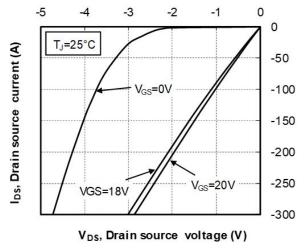
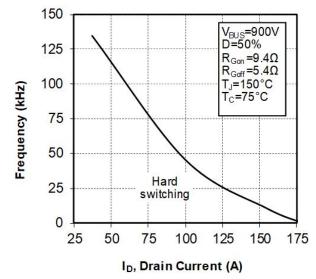


Figure 1-12. Body Diode Characteristics, T_J = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C -3.5 -3 -2.5 -2 -1.5 0 0 V_{GS}=-5V los, Drain source current (A) T_J=175°C current (A) -50 -50 V_{GS}=-2V -100 -100 Ds, Drain source V_{GS}=0V -150 -150 V_{GS}=20V VGS=18V -200 -200 -250 -250 V_{GS}=0V T_J=175°C -300 -300 V_{DS}, Drain source voltage (V) V_{DS}, Drain source voltage (V)

Figure 1-14. Operating Frequency vs Drain Current



1.5 Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM170TLM15CAG device.

Figure 1-15. Maximum Thermal Impedance

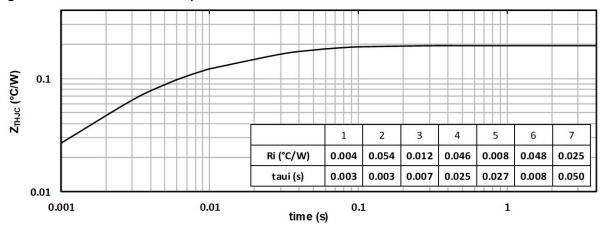


Figure 1-16. Forward Characteristics

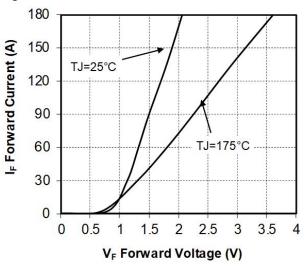
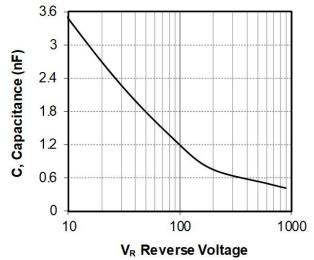


Figure 1-17. Capacitance vs. Reverse Voltage



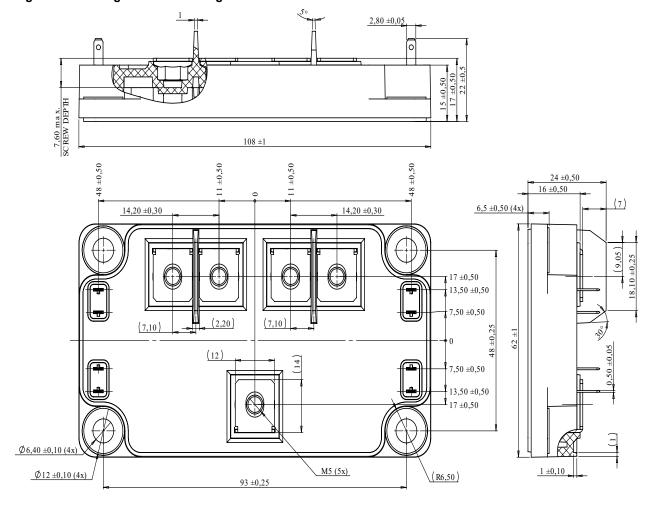
2. Package Specifications

The following section shows the package specification of the MSCSM170TLM15CAG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM170TLM15CAG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



MSCSM170TLM15CAG

Revision History

3. Revision History

Revision	Date	Description
Α	12/2021	This is the first publication of this document.

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